



## STD19NE06

### N-CHANNEL 60V - 0.042 Ω - 19A IPAK/DPAK STripFET™ POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>D(on)</sub>	I <sub>D</sub>
STD19NE06	60 V	<0.050 Ω	19 A

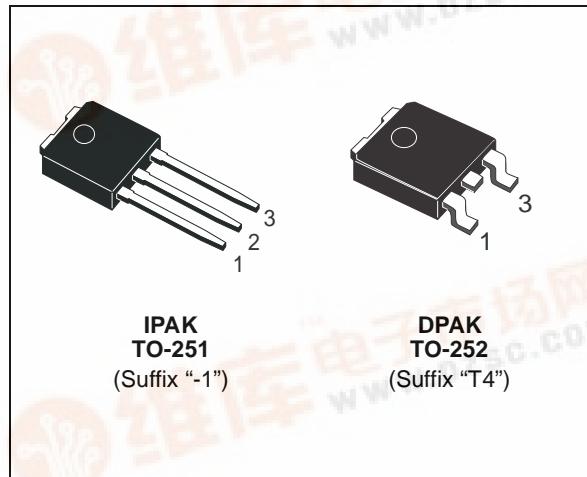
- TYPICAL R<sub>D(on)</sub> = 0.042 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- 175 °C OPERATING TEMPERATURE
- THROUGH-HOLE IPAK (TO-251) POWER PACKAGE IN TUBE (SUFFIX "-1")
- SURFACE-MOUNTING DPAK (TO-252) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")

#### DESCRIPTION

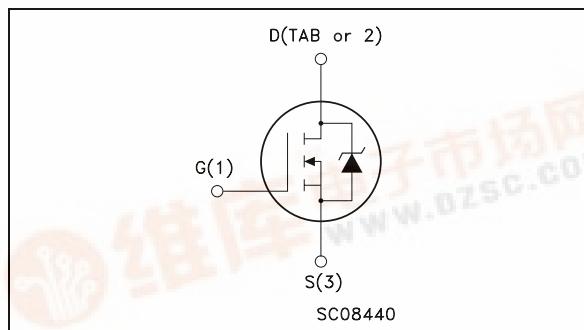
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

#### APPLICATIONS

- DC MOTOR CONTROL
- DC-DC & DC-AC CONVERTERS
- SYNCHRONOUS RECTIFICATION



#### INTERNAL SCHEMATIC DIAGRAM



#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	60	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	60	V
V <sub>GS</sub>	Gate-source Voltage	± 20	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	19	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	13.5	A
I <sub>DM(•)</sub>	Drain Current (pulsed)	76	A
P <sub>tot</sub>	Total Dissipation at T <sub>C</sub> = 25°C	70	W
	Derating Factor	0.46	W/°C
E <sub>AS</sub> (1)	Single Pulse Avalanche Energy	1.45	mJ
T <sub>stg</sub>	Storage Temperature	-55 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature		

(•) Pulse width limited by safe operating area

(1) Starting T<sub>j</sub> = 25 °C, I<sub>D</sub> = 30A, V<sub>DD</sub> = 30 V

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### THERMAL DATA

Rthj-case Rthj-amb T <sub>I</sub>	Thermal Resistance Junction-case Thermal Resistance Junction-ambient Maximum Lead Temperature For Soldering Purpose	Max Max	2.14 100 300	°C/W °C/W °C
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### ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^\circ\text{C}$ unless otherwise specified)

#### OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>C</sub> = 125°C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			±100	nA

#### ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V I <sub>D</sub> = 9.5 A		0.042	0.05	Ω

#### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> = 15 V I <sub>D</sub> = 9.5 A	4	10		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		1450 200 45		pF pF pF

**ELECTRICAL CHARACTERISTICS (continued)****SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{DD} = 30 \text{ V}$ $I_D = 15 \text{ A}$ $R_G = 4.7 \Omega$ $V_{GS} = 10 \text{ V}$ (Resistive Load, Figure 3)		18 95		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 48 \text{ V}$ $I_D = 30 \text{ A}$ $V_{GS} = 10 \text{ V}$		35 10 12	50	nC nC nC

**SWITCHING OFF**

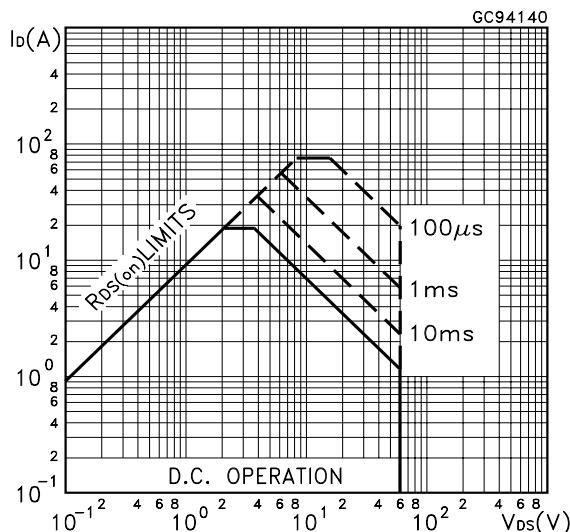
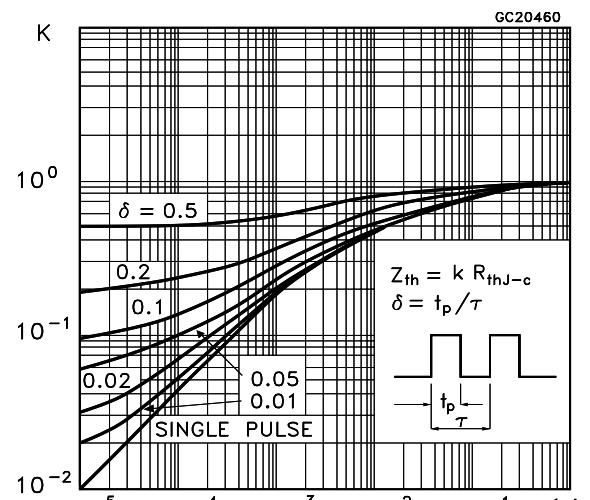
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ $t_f$ $t_c$	Off-voltage Rise Time Fall Time Cross-over Time	$V_{clamp} = 48 \text{ V}$ $I_D = 30 \text{ A}$ $R_G = 4.7 \Omega$ , $V_{GS} = 10 \text{ V}$ (Inductive Load, Figure 5)		10 41 60		ns ns ns

**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				19 76	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 19 \text{ A}$ $V_{GS} = 0$			1.2	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 19 \text{ A}$ $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 30 \text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		85 190 4.5		ns nC A

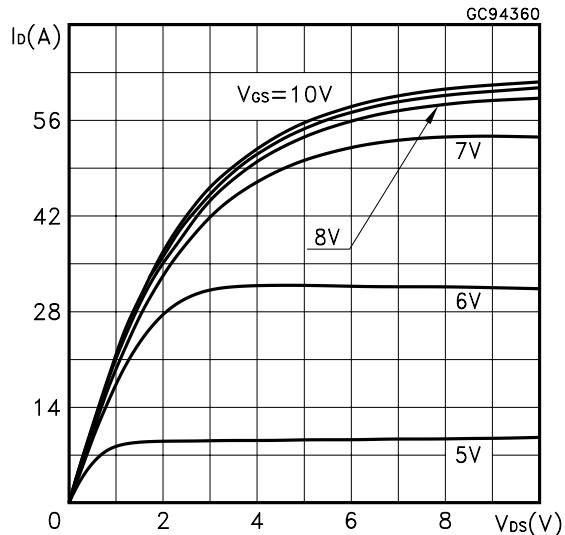
(\*)Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

(\bullet)Pulse width limited by safe operating area.

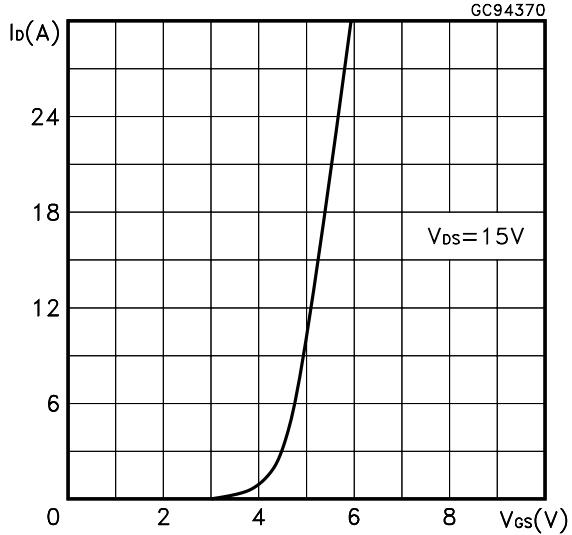
**Safe Operating Area****Thermal Impedance**

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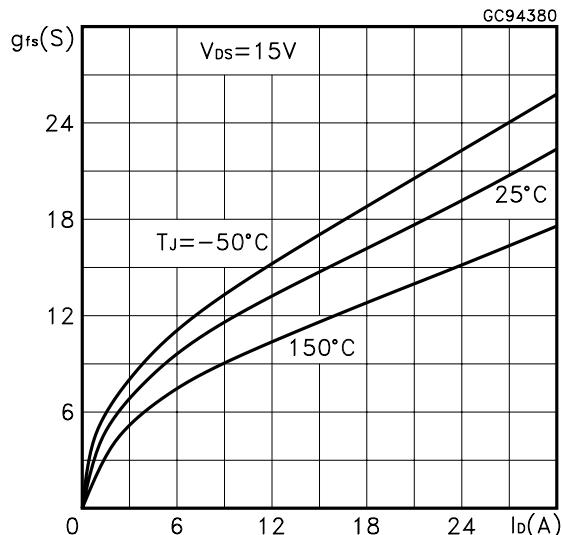
Output Characteristics



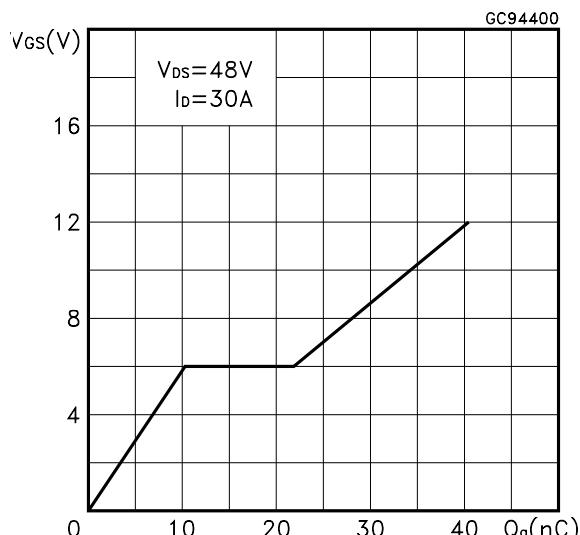
Transfer Characteristics



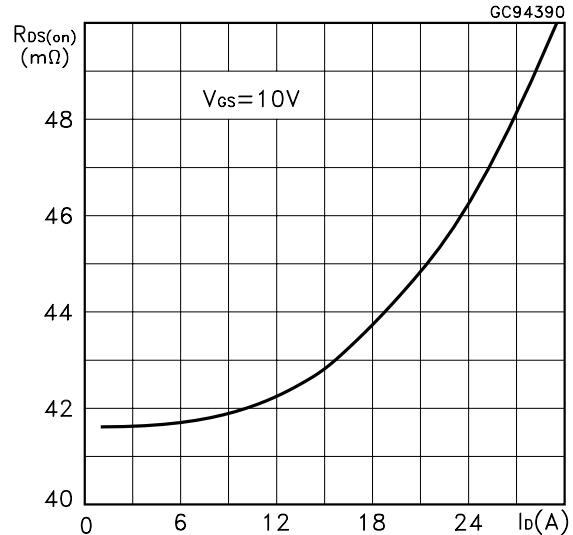
Transconductance



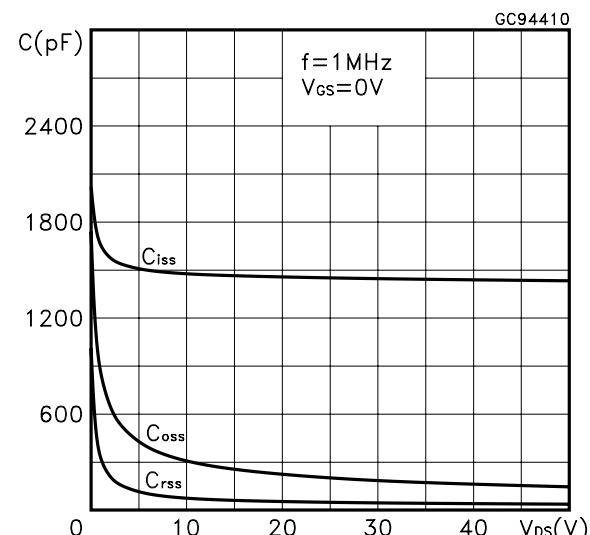
Gate Charge vs Gate-source Voltage



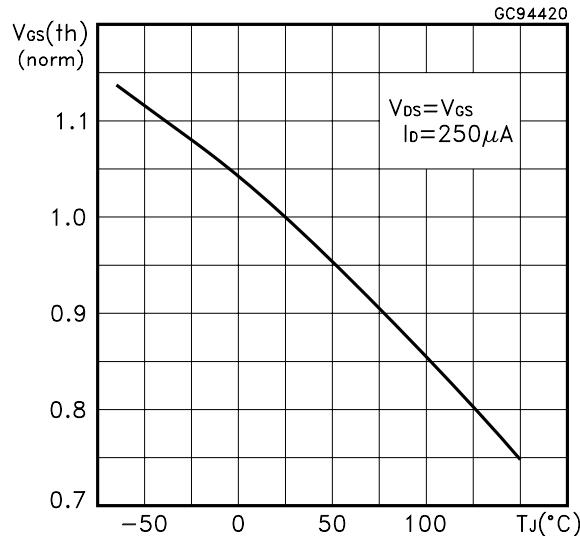
Static Drain-source On Resistance



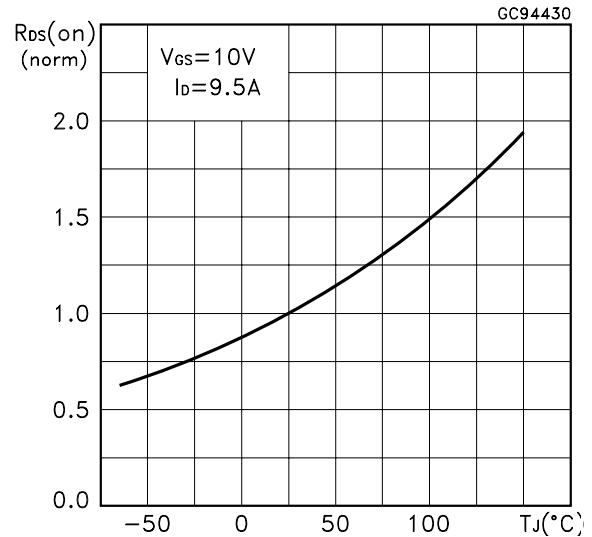
Capacitance Variations



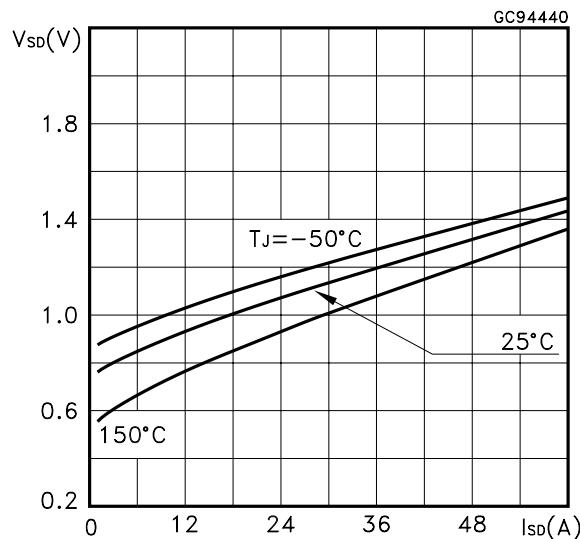
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature

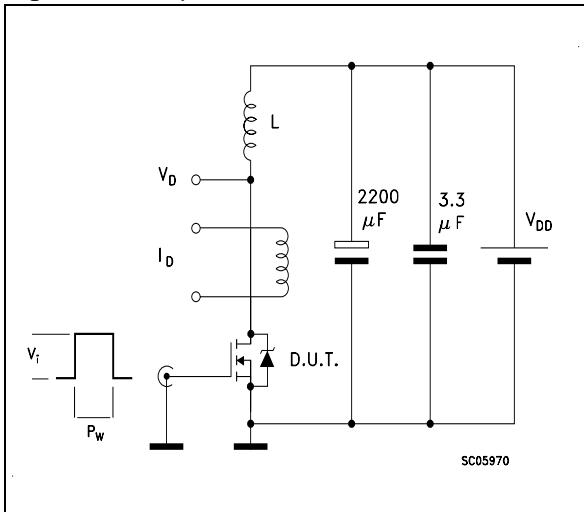


Source-drain Diode Forward Characteristics

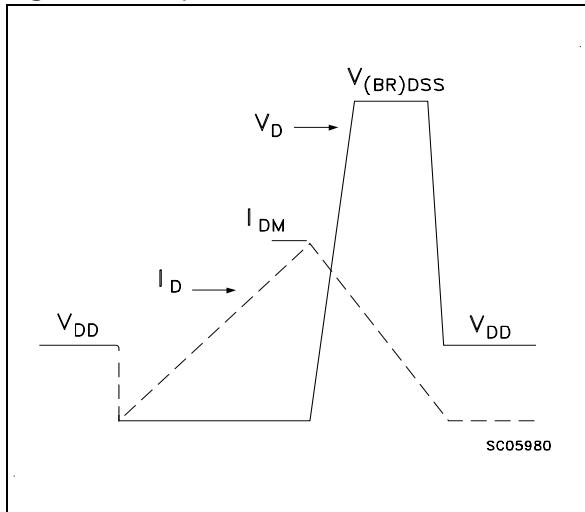


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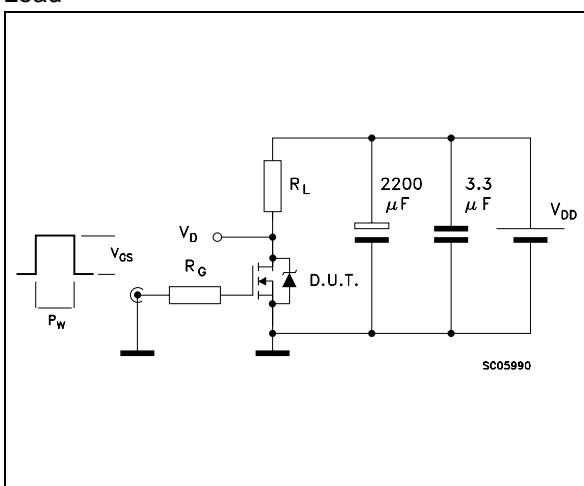
**Fig. 1:** Unclamped Inductive Load Test Circuit



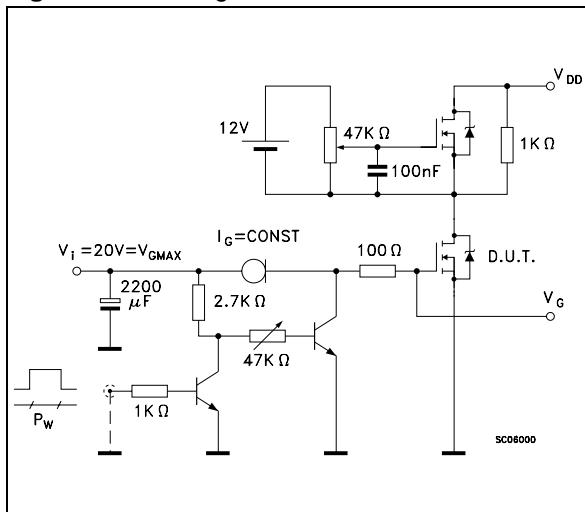
**Fig. 2:** Unclamped Inductive Waveform



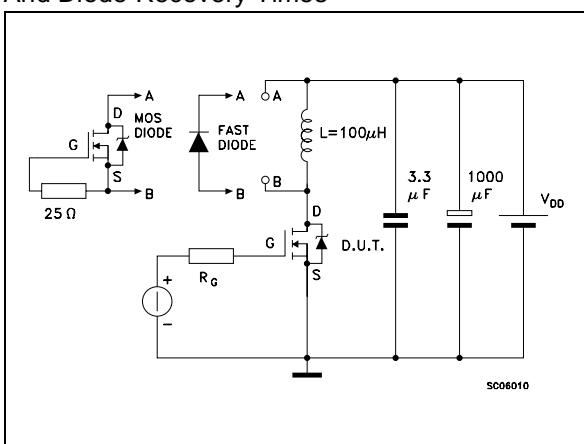
**Fig. 3:** Switching Times Test Circuits For Resistive Load



**Fig. 4:** Gate Charge test Circuit

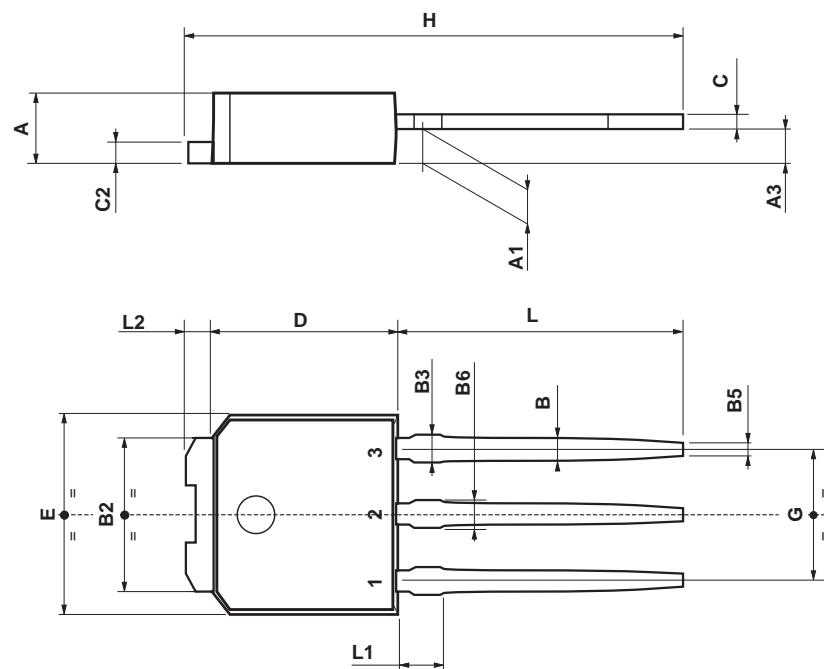


**Fig. 5:** Test Circuit For Inductive Load Switching And Diode Recovery Times



## TO-251 (IPAK) MECHANICAL DATA

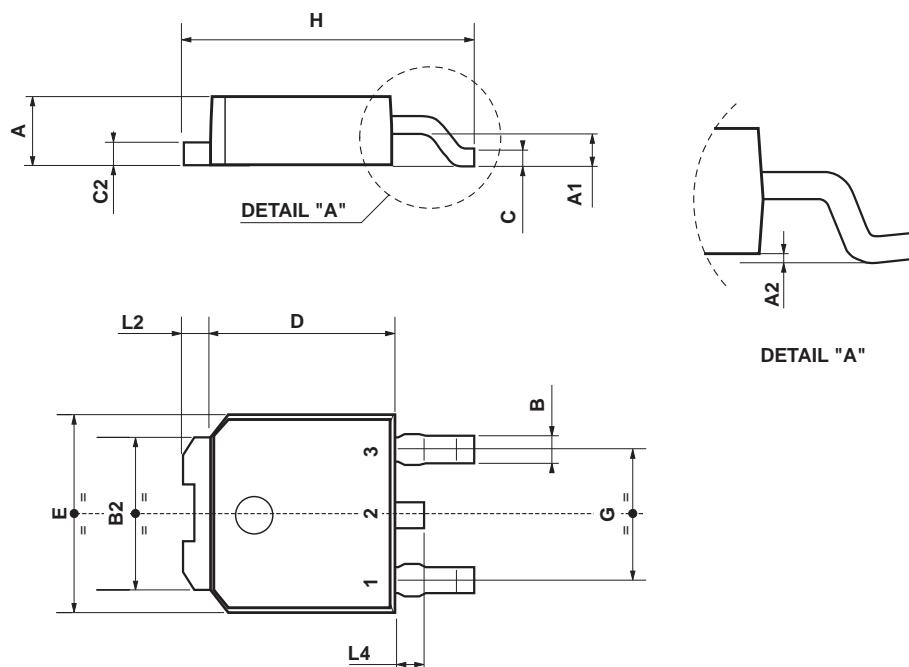
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



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## TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039



0068772-B

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